

### REMARKS

Claims 1-24 are pending. Claims 8, 10, and 16 are herein amended; no other amendments are made. Applicants submit that the amendments do not add new material to the current Application. Claims 8 and 10 are amended to fix grammatical errors and support for amended claim 16 is found on at least page 8, lines 8-10 of Applicants's specification.

No amendment made is related to the statutory requirements of patentability unless expressly stated herein. No amendment made is for the purpose of narrowing the scope of any claims, unless Applicants argue herein that such amendment is made to distinguish over a particular reference or combination of references.

#### Claims Rejections

##### The formalities in claims 8 and 10 have been corrected.

Claim 8 was objected to because Applicants stated, "...selective and substantially..." A change to "...selectively and substantially..." was requested. This change was made in claim 8 and, hence, the objection should be withdrawn.

Claim 10 was objected to because Applicants stated, "...first and second dielectric layers further comprises...third dielectric layer further comprises..." and a change to "...first and second dielectric layers comprises...third dielectric layer comprises..." was requested. While Applicants believe no amendment is necessary, Applicants herein amend claim 10 to hasten prosecution. However, instead of amending claim 10 so that it states, "...first and second dielectric layers comprises...third dielectric layer comprises..." Applicants have amended claim 10 so that it states, "...first and second dielectric layers comprise...third dielectric layer comprises..." so that "comprise" instead of "comprises" is used after "first and second dielectric layers" to comply with English grammar.

Claims 8 and 10 were not amended to distinguish over a particular reference or combination of references.

##### Claim 16 complies with 37 C.F.R. 1.75(c).

Claim 16 was objected to under 37 C.F.R. 1.75(c) as being of improper dependent form for failing to further limit the subject matter of a previous claim. Regardless as to whether Applicants agree with this, Applicants have amended claim 16. Claim 16 limits the subject matter of the previous claim. Claim 16 was not amended to distinguish over a particular reference or combination of references.

Claims 21 and 22 are patentable under 35 U.S.C. 102(b) over Deleonibus (U.S. 6,091,076).

Applicants respectfully submit that claims 21 and 22 are patentable over Deleonibus under 35 U.S.C. 102(b). More specifically, Deleonibus fails to teach or suggest, "epitaxially growing a current electrode over each of the current electrode isolation structures." Deleonibus teaches only depositing current electrodes 92 and 94 over current electrode isolation structures and fails to teach or suggest epitaxially growing the current electrodes. (See col. 7, lines 43-49, col. 10, lines 35-38, and col. 10, lines 59-62.) As shown in Deleonibus's figure 9 and discussed in col. 7, lines 45-61, Deleonibus deposits a metallic material over the entire structure and then polishes the metallic material to form the current electrodes 92 and 94. Thus, the deposition is a global application of the metallic material. In contrast, epitaxial growth is a selective process meaning the material is only grown on selective areas based on the chemistry of the area. Since Deleonibus teaches away from a selective process by teaching a process that is the opposite, a global process, Deleonibus does not teach, "epitaxially growing a current electrode." For at least this reason, independent claim 21 and dependent claims 22 are not anticipated by Deleonibus under 35 U.S.C. 102(b).

Furthermore, Applicants submit that the invention recited in claims 21 and 22 are not obvious in view Deleonibus. As previously mentioned, Deleonibus does not teach or suggest epitaxially growing a current electrode 400, because Deleonibus's metallic material is formed on the entire surface of the wafer and is not selectively formed as is the case with epitaxial growth.

Furthermore, no rejection was made of claims 1-7, 9, 11-15, and 17-20. The Examiner instead stated, "Claims 1-20 would be allowable if applicants submit correction and/or arguments regarding objections on claims 8, 10, and 16." Therefore, no arguments are believed to be needed with respect to claims 1-7, 9, 11-15, and 17-20. In addition, claims 23 and 24 were objected to due to the rejection of claims 20 and 22 and therefore, no additional arguments are needed.

Believing to have responded to every issue raised by the Examiner in the last communication mailed, Applicants believe the present Application is currently in a condition of allowance. Applicants earnestly solicit allowance of all pending claims. Please contact Applicant's practitioner listed below if there are any issues.

If Applicant has overlooked any additional fees, or if any overpayment has been made, the Commissioner is hereby authorized to credit or debit Deposit Account 503079, Freescale Semiconductor, Inc.

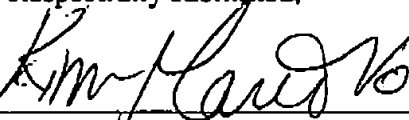
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Respectfully submitted,

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